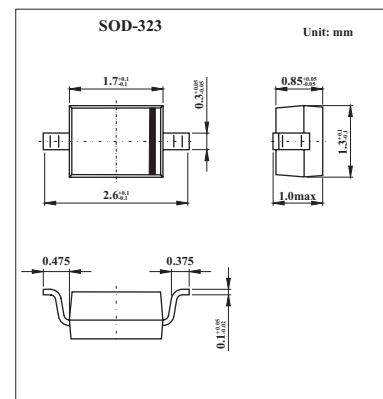


## Schottky barrier Diodes

## 1PS76SB21

## ■ Features

- Ultra fast switching speed
- Low forward volatge
- Guard ring protected
- Very small plastic SMD package.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

PARAMATER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
continuous reverse voltage	$V_R$			4	V
continuous forward current	$I_F$			200	mA
non-repetitive peak forward current	$I_{FSM}$	$t_p < 10 \text{ ms}$		1	A
storage temperature	$T_{stg}$		-65	+150	$^\circ\text{C}$
junction temperature	$T_j$			125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

PARAMATER	SYMBOL	CONDITIONS	MIN.	MAX.	UNIT
forward volatge	$V_F$	$I_F = 10 \text{ mA}$		300	mV
		$I_F = 100 \text{ mA}$		420	mV
		$I_F = 200 \text{ mA}$		550	mV
reverse current	$I_R$	$V_R = 30 \text{ V}; \text{note 1}$		15	$\mu\text{A}$
		$V_R = 30 \text{ V}; T_j = 100^\circ\text{C}, \text{note 1}$		3	mA
diode capacitance	$C_d$	$f = 1 \text{ MHz}; V_R = 0 \text{ V};$	40	50	pF
thermal resistance from junction to ambient	$R_{thj-a}$			450	K/W

Note

## ■ Marking

Marking	S1
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